EVVOSEMI®
THINK CHANGE DO

ESD TVS MOS LDO Diode Sensor DC-DC

Product Specification

Domestic Part Number	PSMN017-80B
Overseas Part Number	PSMN017-80B
Equivalent Part Number	PSMN017-80B

N-Ch 80V Fast Switching MOSFETs

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

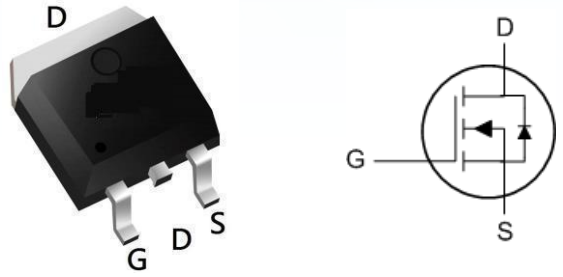
Product Summary

BVDSS	RDSON	ID
80V	6.5mΩ	108A

Description

The PSMN017-80B is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.
The PSMN017-80B meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO263 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	80	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	108	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	68	A
I_{DM}	Pulsed Drain Current[2]	200	A
EAS	Single Pulse Avalanche Energy[3]	125	mJ
I_{AS}	Avalanche Current	50	A
P_D@T_C=25℃	Total Power Dissipation[4]	149	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	55	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	0.84	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	80	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=54A	---	---	6.5	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	2.5	---	4.5	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=64V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=64V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=30A	---	50	---	S
Qg	Total Gate Charge (10V)	V_{DS}=64V , V_{GS}=10V , I_D=30A	---	83.7	---	nC
Qgs	Gate-Source Charge		---	28.6	---	
Qgd	Gate-Drain Charge		---	29.3	---	
Td(on)	Turn-On Delay Time	V_{DD}=40V , V_{GS}=10V , R_G=3.3Ω, I_D=30A	---	38.1	---	ns
Tr	Rise Time		---	73.3	---	
Td(off)	Turn-Off Delay Time		---	51.6	---	
Tf	Fall Time		---	26.1	---	
Ciss	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	5580	---	pF
Coss	Output Capacitance		---	571	---	
Crss	Reverse Transfer Capacitance		---	278	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	70	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	I_F=30A , dI/dt=100A/μs , T_J=25℃	---	26.7	---	nS
Q_{rr}	Reverse Recovery Charge		---	27.9	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=50A
4.The power dissipation is limited by 150℃ junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.
6.Package limitation current is 70A.

Typical Characteristics

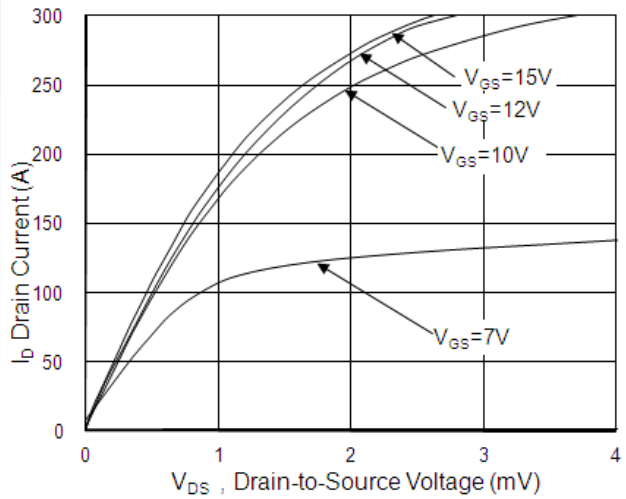


Fig.1 Typical Output Characteristics

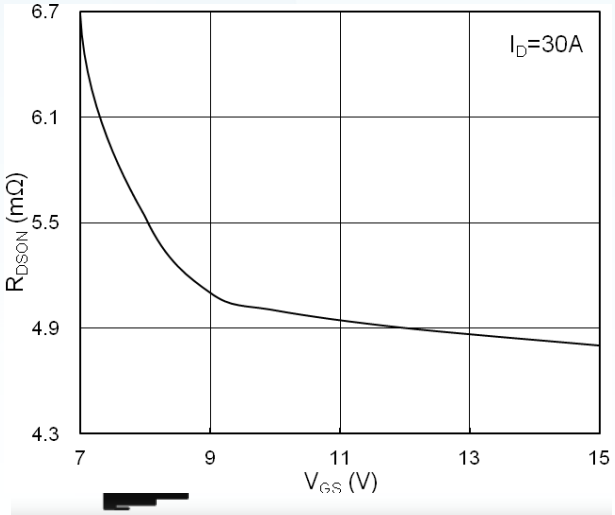


Fig.2 On-Resistance vs. G-S Voltage

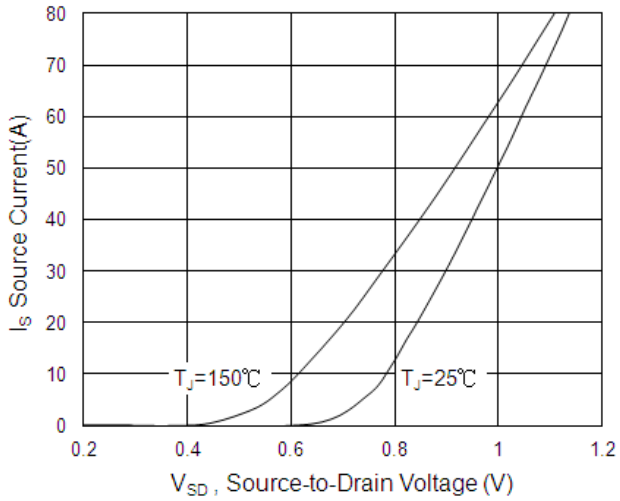


Fig.3 Source Drain Forward Characteristics

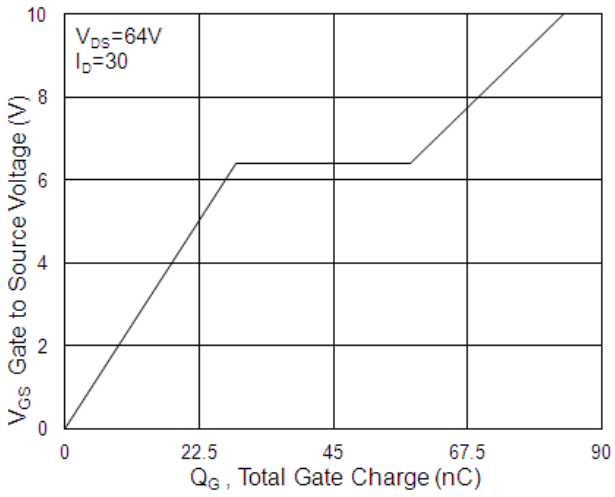


Fig.4 Gate-Charge Characteristics

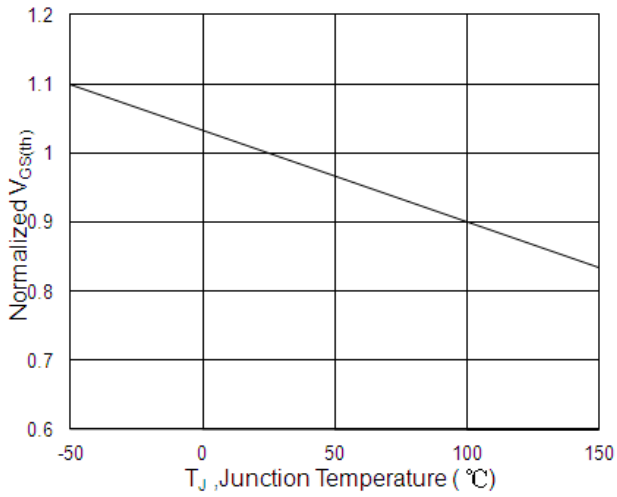


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

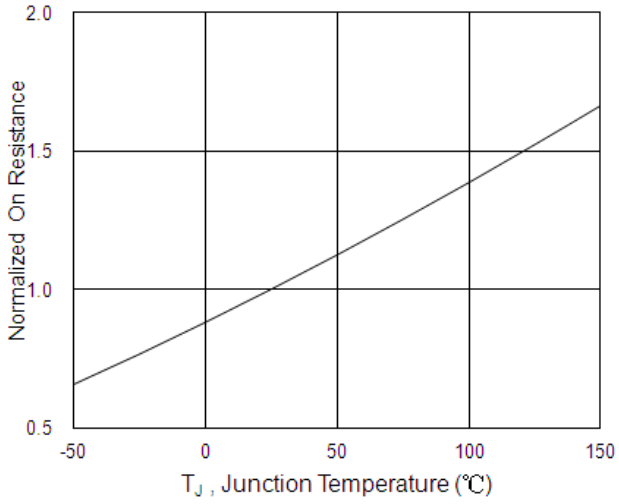


Fig.6 Normalized R_{DSON} vs. T_J

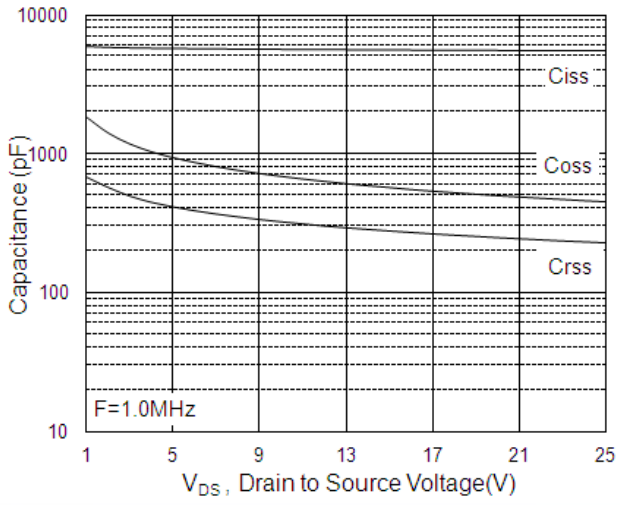


Fig.7 Capacitance

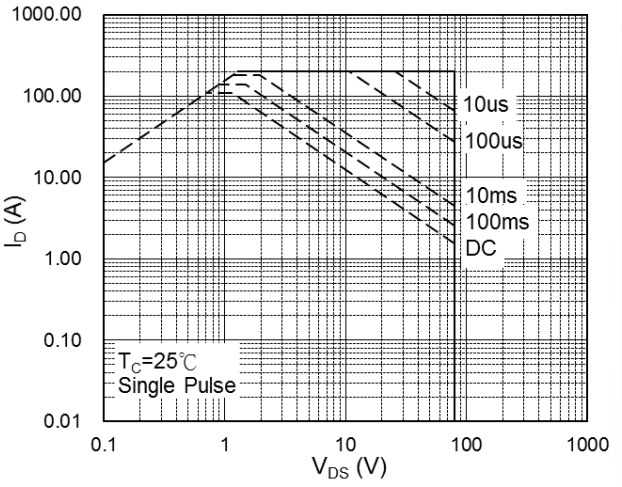


Fig.8 Safe Operating Area

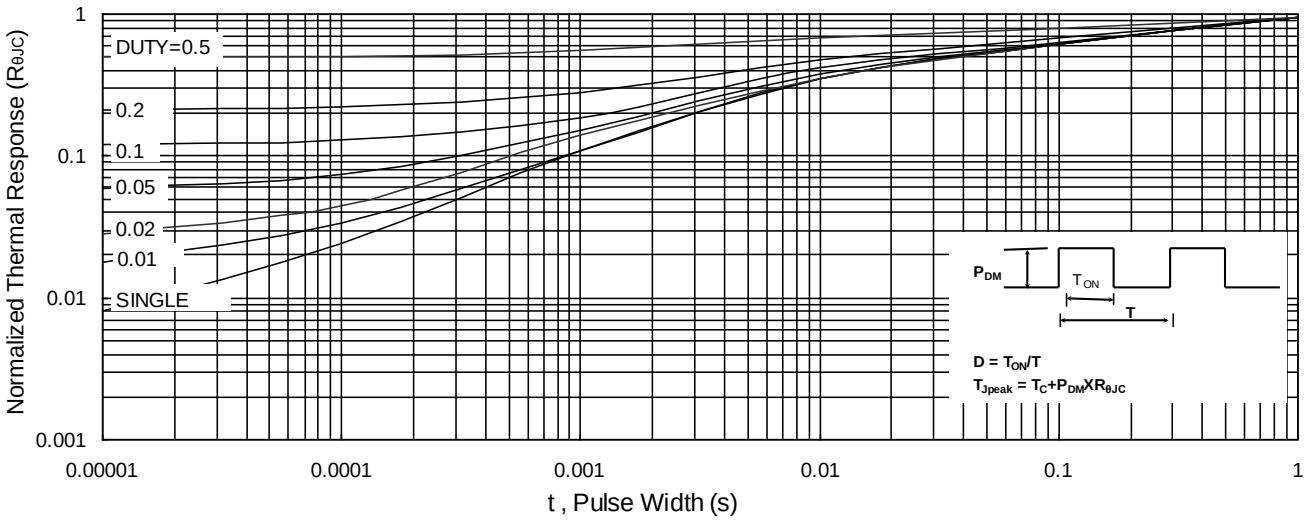


Fig.9 Normalized Maximum Transient Thermal Impedance

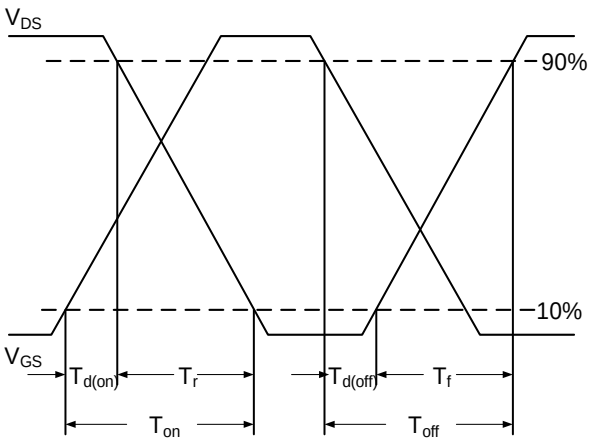


Fig.10 Switching Time Waveform

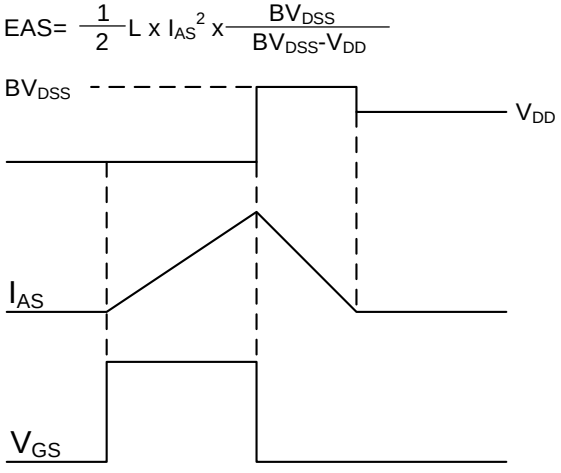
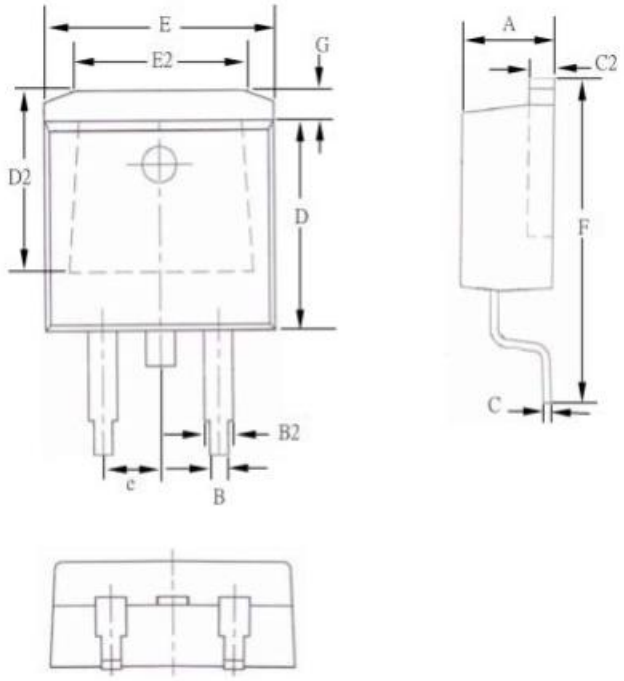


Fig.11 Unclamped Inductive Switching Waveform

TO263 Package Outline Dimensions



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM		MIN	NOM	
A	4.06	—	4.83	0.160	—	0.190
B	0.51	—	0.99	0.020	—	0.039
B2	1.14	—	1.78	0.045	—	0.070
C	0.34	—	0.74	0.013	—	0.029
C2	1.14	—	1.65	0.045	—	0.065
D	8.38	—	9.65	0.330	—	0.380
D2	6.86	—	7.86	0.270	—	0.309
E	9.65	—	10.67	0.380	—	0.420
E2	6.22	—	7.40	0.245	—	0.291
F	13.08	—	15.50	0.515	—	0.610
G	0.68	—	1.68	0.027	—	0.066
e	—	2.54	—	—	0.100	—

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